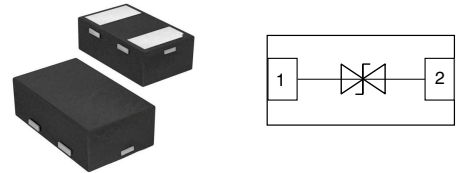


Low Capacitance ESD Protection Diode in DFN1006

Features

- 150Watts peak pulse power ($T_P = 8/20\mu s$)
- DFN1006 package
- Bidirectional configurations
- Low clamping voltage
- Low leakage current
- Low capacitance ($C_j = 3.3pF$ typ.)
- Protection one data/power line to:
 - IEC 61000-4-2 $\pm 8kV$ contact $\pm 15kV$ air
 - IEC 61000-4-4 (EFT) 40A (5/50ns)
 - IEC 61000-4-5 (Lightning) 6A (8/20 μs)



Mechanical Data

- **Case:** DFN1006 (plastic package).
Lead free; RoHS compliant; Halogen free
- **Molding Compound Flammability Rating:**
UL 94 V-0
- **Terminals:** High temperature soldering guaranteed:
260 °C/10 sec. at terminals

Applications

- Microprocessor based equipment
- Personal Digital Assistants(PDA's)
- Notebooks, Desktops and Servers
- Portable Instrumentation
- Pagers Peripherals

Absolute Maximum Ratings

Ratings at 25 °C, ambient temperature unless otherwise specified

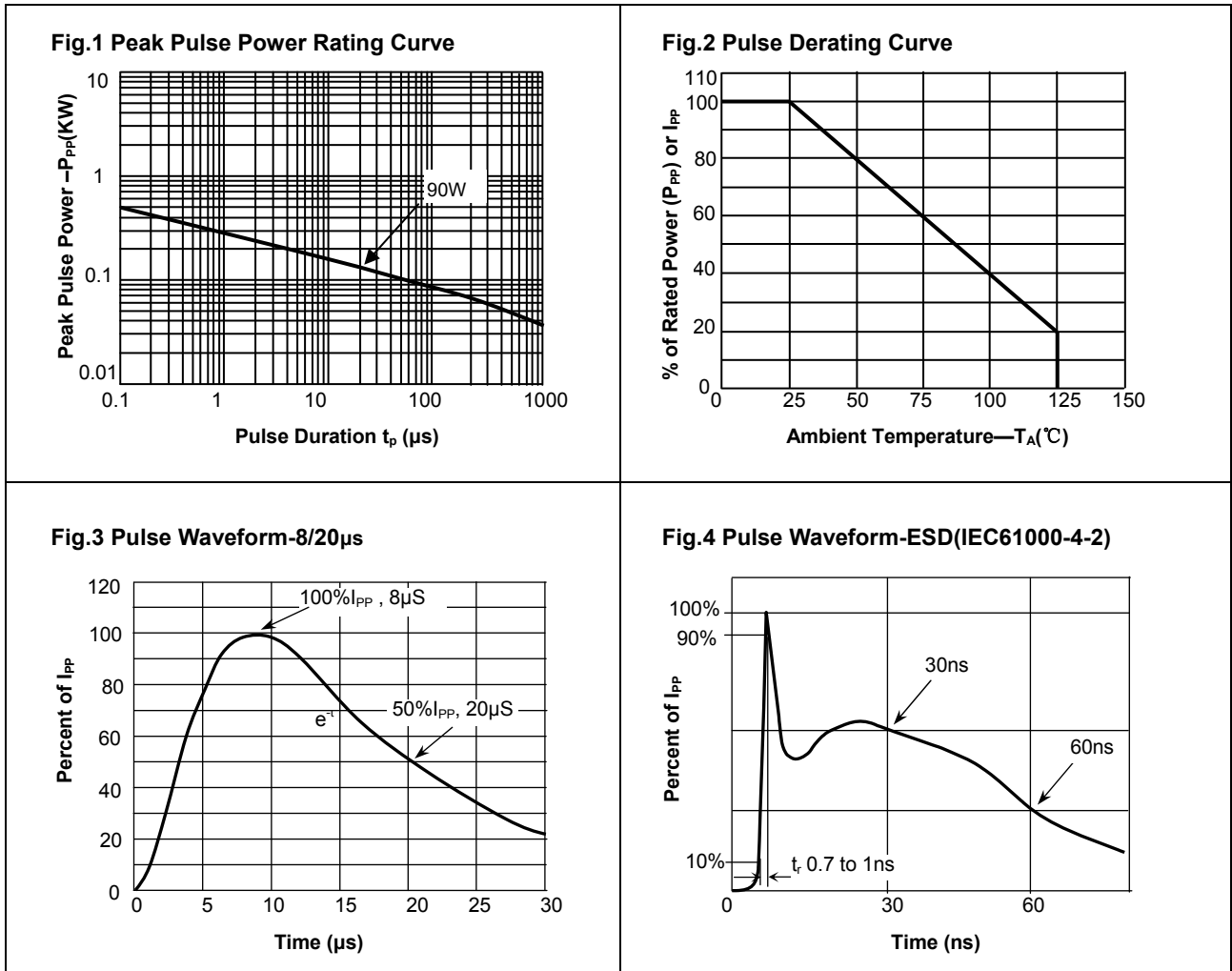
Parameter	Symbol	Value	Unit
Peak Pulse Power ($T_P = 8/20\mu s$)	P_{PP}	150	W
ESD contact/air discharge (IEC-61000-4-2)	V_{ESD}	8/15	kV
Peak Pulse Current ($T_P = 8/20\mu s$)	I_{PP}	6	A
Junction Temperature	T_J	-55 to +125	°C
Storage temperature	T_{STG}	-55 to +150	°C

Electrical Characteristics

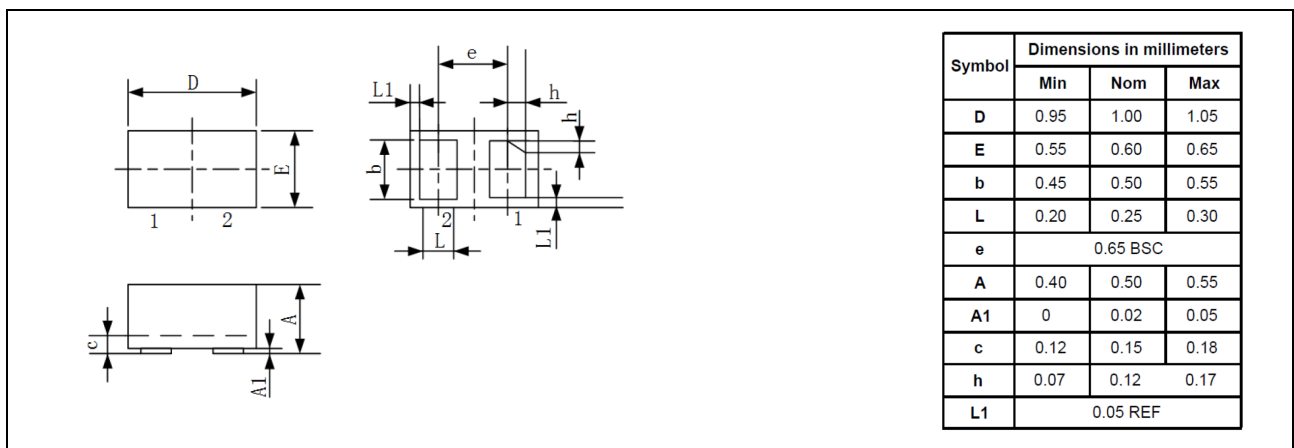
($T_A = 25$ °C unless otherwise specified)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Reverse stand-off Voltage	V_{RWM}				12	V
Reverse Breakdown Voltage	V_{BR}	$I_T = 1mA$	12.1			V
Reverse Leakage Current	I_R	$V_R = 12V$			0.5	μA
Clamping Voltage (IEC 61000-4-5)	V_C	$I_{PP} = 6A$		25		V
Junction Capacitance	C_J	$V_R = 0V, f = 1MHz$		3.3		pF

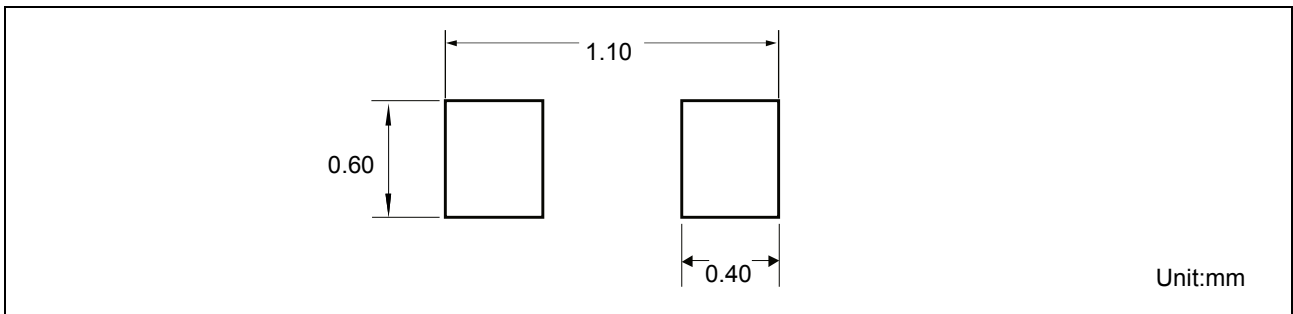
Typical Characteristics ($T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)



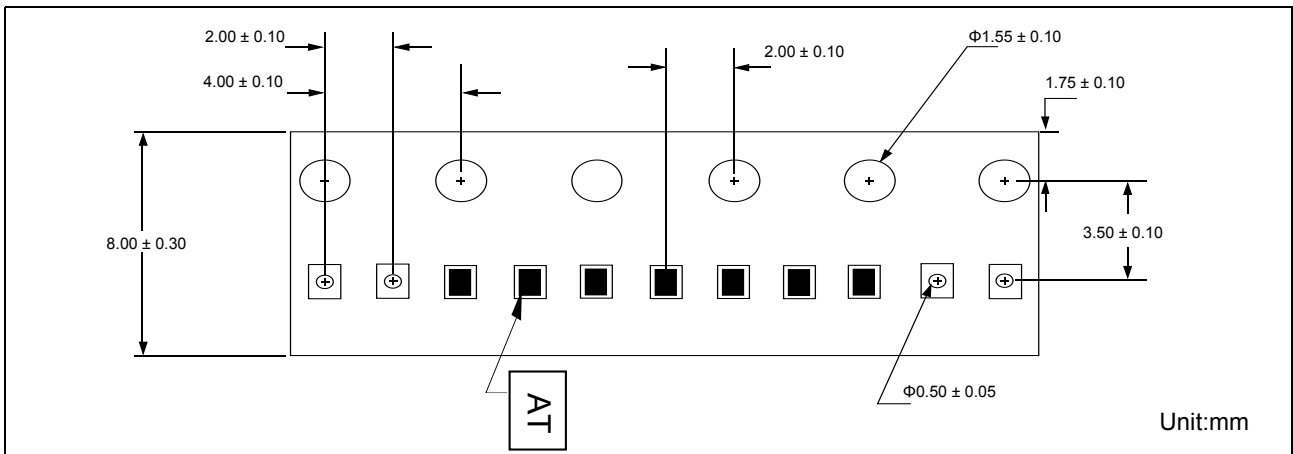
Package Dimensions



Pad Dimensions



Tape and Reel Specification



Marking



Ordering information

Order code	Package	Packaging option	Base quantity	Packaging specification
TESD1006LC12VB	DFN1006	Tape and reel	10000pcs / reel	EIA STD RS-481